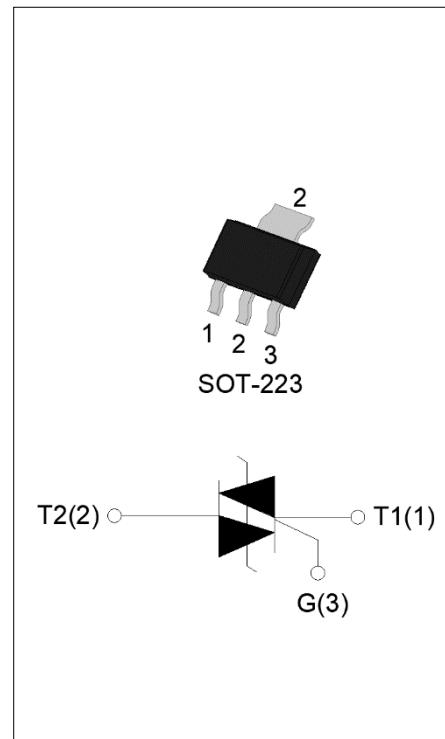




The ACJT105-8V triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. The ACJT105-8V embeds a TVS structure to absorb the inductive turn-off energy such as those described in the IEC 61000-4-5 standards. Package SOT-223 is RoHS compliant.

Symbol	Value	Unit
$I_{T(RMS)}$	1	A
$V_{DRM}/V_{RRM}$	800	V
$I_{GT} / /$	5/5/5	mA



Parameter	Symbol	Value	Unit
Storage junction temperature range	$T_{stg}$	-40-150	
Operating junction temperature range	$T_j$	-40-125	
Repetitive peak off-state voltage ( $T_j=25^\circ C$ )	$V_{DRM}$	800	V
Repetitive peak reverse voltage ( $T_j=25^\circ C$ )	$V_{RRM}$	800	V
RMS on-state current ( $T_c = 90^\circ C$ )	$I_{T(RMS)}$	1	A
Non repetitive surge peak on-state current (full cycle , $t_p=20ms$ , $T_j=25^\circ C$ )	$I_{TSM}$	15	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6ms$ , $T_j=25^\circ C$ )		16.5	
$I^2t$ value for fusing ( $t_p=10ms$ , $T_j=25^\circ C$ )	$I^2t$	1.25	$A^2s$
Critical rate of rise of on-state current ( $I_G=2mA$ , $I_{GT}$ , $f=100Hz$ , $T_j=125^\circ C$ )	$dI/dt$	50	$A/\mu s$
Peak gate current ( $t_p=20\mu s$ , $T_j=125^\circ C$ )	$I_{GM}$	2	A
Average gate power dissipation ( $T_j=125^\circ C$ )	$P_{G(AV)}$	0.1	W
Peak gate power	$P_{GM}$	5	W

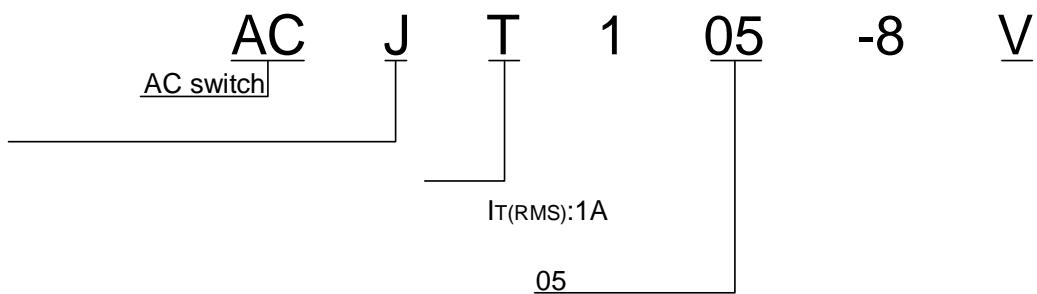
Peak pulse voltage (T <sub>j</sub> =25 °C; non-repetitive, off-state; FIG.8)	V <sub>pp</sub>	3.5	kV
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(T<sub>j</sub>=25 °C unless otherwise specified)

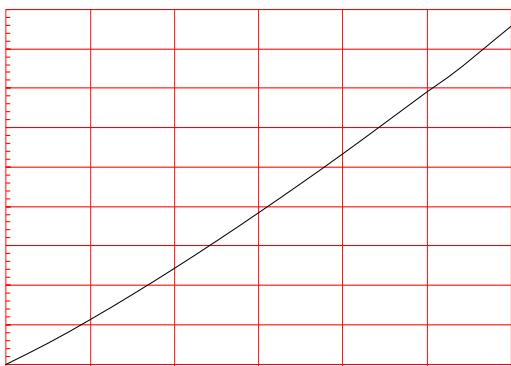
Symbol	Test Condition	Quadrant	Value		Unit
I <sub>GT</sub>	V <sub>D</sub> =12V R <sub>L</sub> =33	- -	MAX.	5	mA
V <sub>GT</sub>		- -	MAX.	1	V
V <sub>GD</sub>	V <sub>D</sub> =V <sub>DRM</sub> T <sub>j</sub> =125 °C R <sub>L</sub> =3.3K	- -	MIN.	0.2	V

I

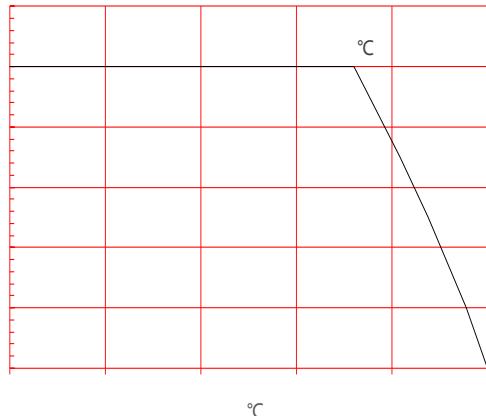




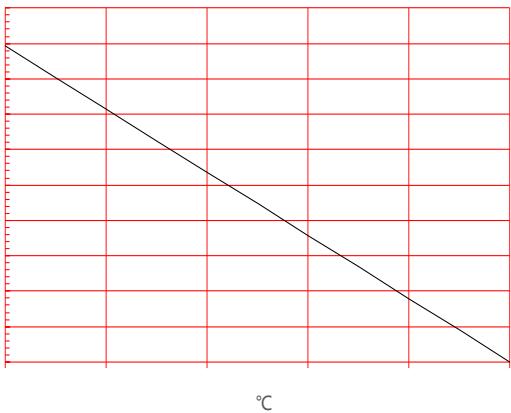
**FIG.1** Maximum power dissipation versus RMS on-state current



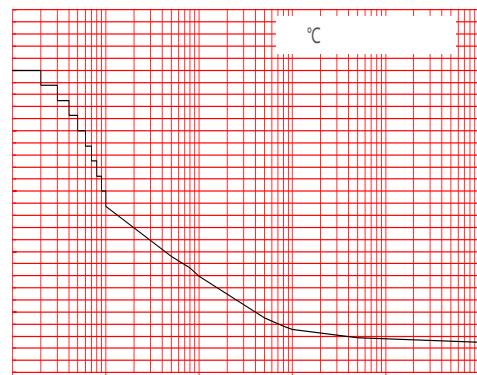
**FIG.2:** RMS on-state current versus case temperature



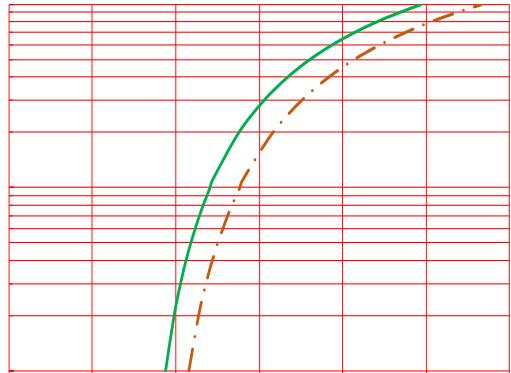
**FIG.3:** RMS on-state current versus ambient temperature (printed circuit board FR4,copper thickness:35μm)(full cycle)



**FIG.4:** Surge peak on-state current versus number of cycles



**FIG.5:** On-state characteristics



**FIG.6:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 20\text{ms}$ , and corresponding value of  $I^2t$  ( $dI/dt < 50\text{A}/\mu\text{s}$ )

**FIG.7:** Relative variations of gate trigger current, holding current and latching current versus junction temperature

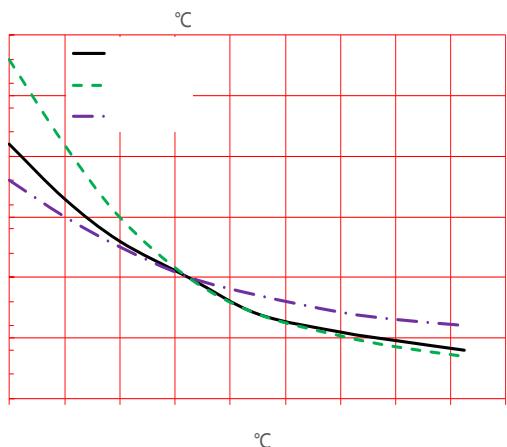
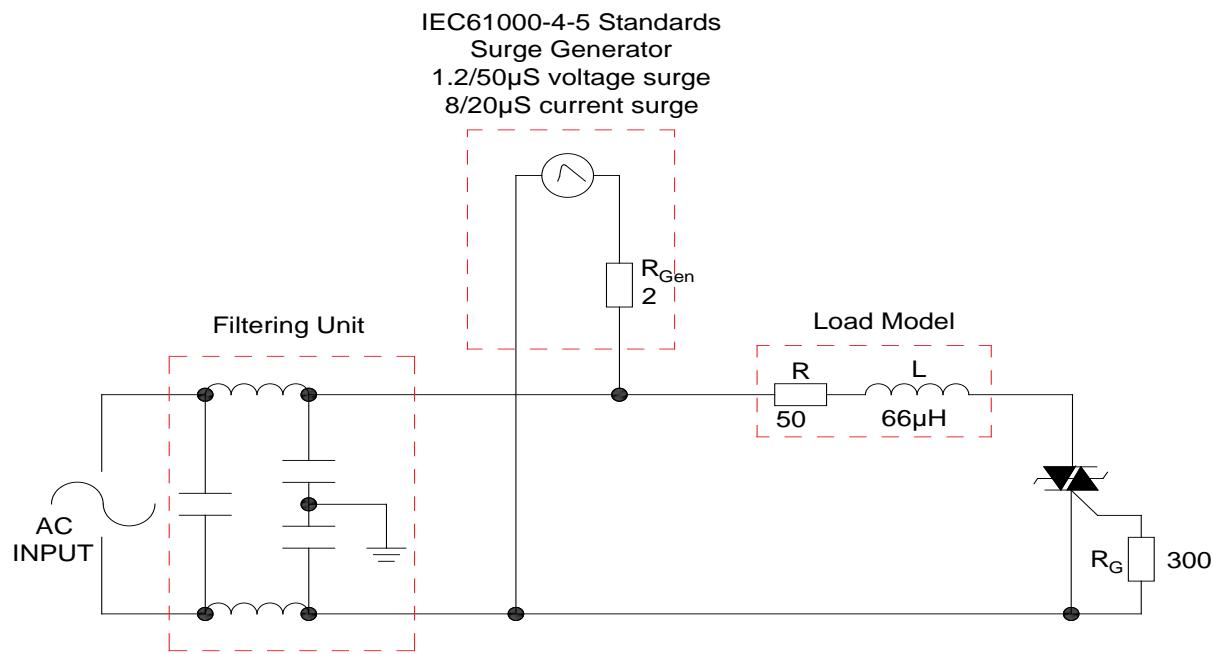


FIG.8 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



Reflow Condition		Pb-Free assembly (see figure at right)
Pre Heat	-Temperature Min ( $T_{s(min)}$ )	+150
	-Temperature Max( $T_{s(max)}$ )	+200
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquidus Temp ( $T_L$ ) to peak)		3 /sec. Max

-e.76 273.36 Tm ( )Tj -0.0027e247200

$T_{s(max)}$  to  $T_L$  - Ramp-up Rate      3 /sec. Max -      up +200

Order code	Voltage $V_{DRM}/V_{RRM}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
ACJT105-8V	800	5	SOT-223	4,000	Tape & Reel

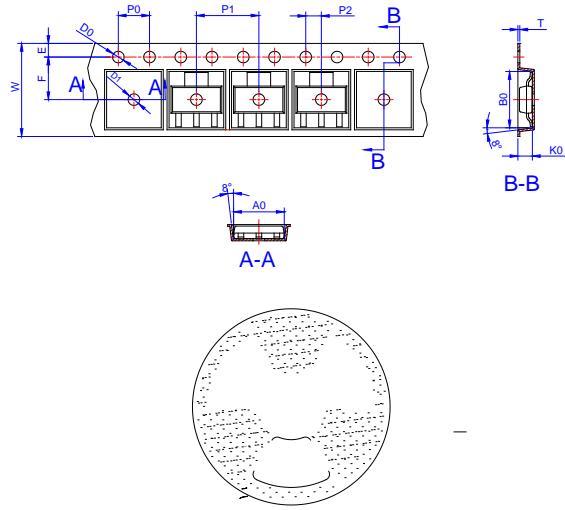
#### Document Revision History

Date	Revision	Changes
Apr.13, 2023	A.1.0	Last updated

**ACJT105-8V**

 **JieJie Microelectronics Co., Ltd.**

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Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	-	-	12.30	-		0.482
E	1.65	1.75	1.85	0.065	0.069	0.073
F	5.45	5.50	5.55	0.215	0.217	0.219
D0	1.50	1.55	1.60	0.059	0.061	0.063
D1	1.50	-	-	0.059	-	-
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.95	2.00	2.05	0.077	0.079	0.081
10P0	39.80	40.00	40.20	1.567	1.575	1.583
A0	6.85	6.95	7.05	0.269	0.273	0.276
B0	7.15	7.25	7.35	0.280	0.284	0.288
K0	1.95	2.05	2.15	0.076	0.080	0.084
T	0.20	0.25	0.30	0.008	0.010	0.012

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